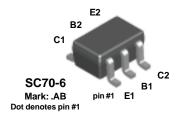
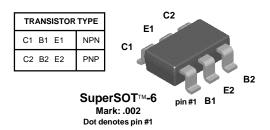


FFB3946

FMB3946





NPN & PNP General Purpose Amplifier

This complementary device is designed for use as a general purpose amplifier and switch The useful dynamic range extends to 100 mA as a switch and 100 MHz as an amplifier. Sourced from Process 23 and 66. See FFB3904 (NPN) and FFB3906 (PNP) for characteristics.

Absolute Maximum Ratings* T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	40	V	
V _{CBO}	Collector-Base Voltage	40	V	
V _{EBO}	Emitter-Base Voltage	5.0	V	
I _C	Collector Current - Continuous	200	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics T_A = 25°C unless otherwise noted

Symbol	Characteristic Max		Units	
		FFB3946	FMB3946	
P _D	Total Device Dissipation	300	700	mW
	Derate above 25°C	2.4	5.6	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	415	180	°C/W

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NPN & PNP General Purpose Amplifier

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Electri	cai v	Jua	ıacıe	HIDLIGS

T_A = 25°C unless otherwise noted

	A					
Symbol	Parameter Test Conditions Min Ty		Тур	Max	Units	
OFF CHAP	RACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	40			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	40			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0			V
I _{CBO}	Collector Cutoff Current	V _{CB} = 30 V, I _E = 0			50	nA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$			50	nA
	<u> </u>					

ON CHARACTERISTICS

h _{FE}	DC Current Gain	$\begin{array}{l} I_C = 100 \; \mu A, \; V_{CE} = 1.0 \; V \\ I_C = 1.0 \; mA, \; V_{CE} = 1.0 \; V \\ I_C = 10 \; mA, \; V_{CE} = 1.0 \; V \\ I_C = 50 \; mA, \; V_{CE} = 1.0 \; V \\ I_C = 100 mA, \; V_{CE} = 1.0 \; V \\ \end{array}$	40 70 100 60 30	300	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		0.25	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 10 mA, I _B = 1.0 mA		0.9	V

SMALL SIGNAL CHARACTERISTICS

f⊤	Current Gain - Bandwidth Product	I _C = 10 mA, V _{CE} = 20 V, f = 100 MHz	200	MHz
C _{obo}	Output Capacitance	$V_{CB} = 5.0 \text{ V}, f = 100 \text{ kHz}$	4.5	pF
C _{ibo}	Input Capacitance	V _{CB} = 5.0 V, f = 100 kHz	10	pF

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

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Definition of Terms

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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